



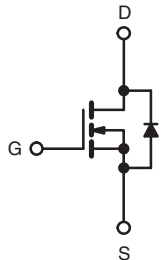
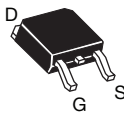
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IRFR010, SiHFR010

Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	50	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.20
Q_g (Max.) (nC)	10	
Q_{gs} (nC)	2.6	
Q_{gd} (nC)	4.8	
Configuration	Single	

DPAK
(TO-252)



N-Channel MOSFET

FEATURES

- Low Drive Current
- Surface Mount
- Fast Switching
- Ease of Paralleling
- Excellent Temperature Stability
- Compliant to RoHS Directive 2002/95/EC



RoHS*
COMPLIANT

DESCRIPTION

The Power MOSFET technology is the key to Vishay's advanced line of Power MOSFET transistors. The efficient geometry and unique processing of this latest "State of the Art" design achieves: very low on-state resistance combined with high transconductance; superior reverse energy and diode recovery dV/dt capability.

The Power MOSFET transistors also feature all of the well established advantages of MOSFET'S such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters.

Surface mount packages enhance circuit performance by reducing stray inductances and capacitance. The DPAK (TO-252) surface mount package brings the advantages of Power MOSFET's to high volume applications where PC Board surface mounting is desirable. The surface mount option IRFR9012, SiHFR9012 is provided on 16 mm tape. The straight lead option IRFU9012, SiHFU9012 of the device is called the IPAK (TO-251).

They are well suited for applications where limited heat dissipation is required such as, computers and peripherals, telecommunication equipment, dc-to-dc converters, and a wide range of consumer products.

ORDERING INFORMATION	
Package	DPAK (TO-252)
Lead (Pb)-free	IRFR010PbF SiHFR010-E3
SnPb	IRFR010 SiHFR010

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	50	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25\text{ }^\circ\text{C}$	A	
		$T_C = 100\text{ }^\circ\text{C}$		
Pulsed Drain Current ^a	I_{DM}	33	A	
Avalanche Current ^b	I_{AS}	1.5		
Linear Derating Factor		0.20	W/ $^\circ\text{C}$	
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	25	W
Peak Diode Recovery dV/dt ^c		dV/dt	2.0	V/ns
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25\text{ V}$, starting $T_J = 25\text{ }^\circ\text{C}$, $L = 100\text{ }\mu\text{H}$, $R_g = 25\text{ }\Omega$.
- $I_{SD} \leq 8.2\text{ A}$, $di/dt \leq 130\text{ A}/\mu\text{s}$, $V_{DD} \leq 40\text{ V}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	-	110	°C/W
Case-to-Sink	R_{thCS}	-	1.7	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	-	5.0	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		50	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 500	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}$		-	-	250	μA
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	1000	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 4.6\text{ A}^b$	-	0.16	0.20	Ω
Forward Transconductance	g_{fs}	$V_{DS} \geq 50\text{ V}, I_D = 3.6\text{ A}$		2.1	3.1	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz},$ see fig. 10		-	250	-	μF
Output Capacitance	C_{oss}			-	150	-	
Reverse Transfer Capacitance	C_{rss}			-	29	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 7.3\text{ A}, V_{DS} = 40\text{ V},$ see fig. 6 and 13 ^b	-	6.7	10	nC
Gate-Source Charge	Q_{gs}			-	1.8	2.6	
Gate-Drain Charge	Q_{gd}			-	3.2	4.8	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 25\text{ V}, I_D = 7.3\text{ A},$ $R_g = 24\text{ }\Omega, R_D = 3.3\text{ }\Omega,$ see fig. 10 ^b		-	11	17	ns
Rise Time	t_r			-	33	50	
Turn-Off Delay Time	$t_{d(off)}$			-	12	18	
Fall Time	t_f			-	23	35	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact ^c		-	4.5	-	nH
Internal Source Inductance	L_S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	8.2	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	33	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 8.2\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.6	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 7.3\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		41	86	190	ns
Body Diode Reverse Recovery Charge	Q_{rr}			0.15	0.33	0.78	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.



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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

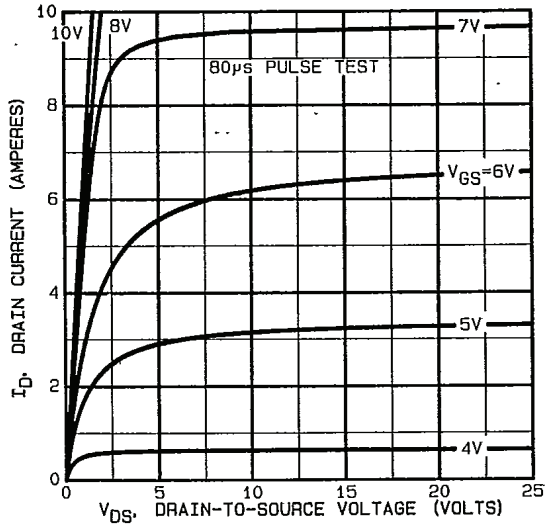


Fig. 1 - Typical Output Characteristics

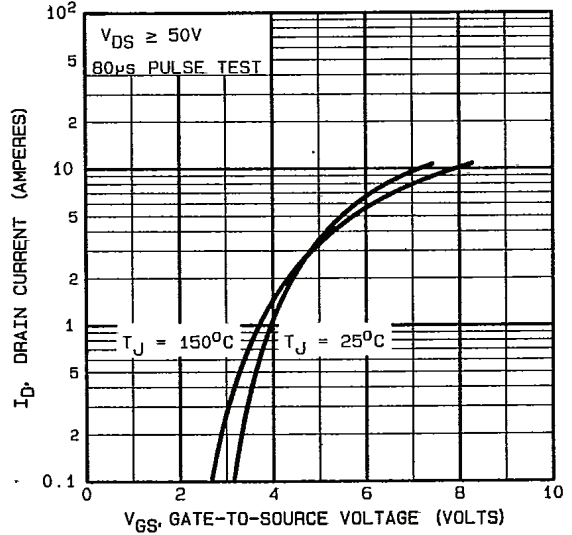


Fig. 3 - Typical Transfer Characteristics

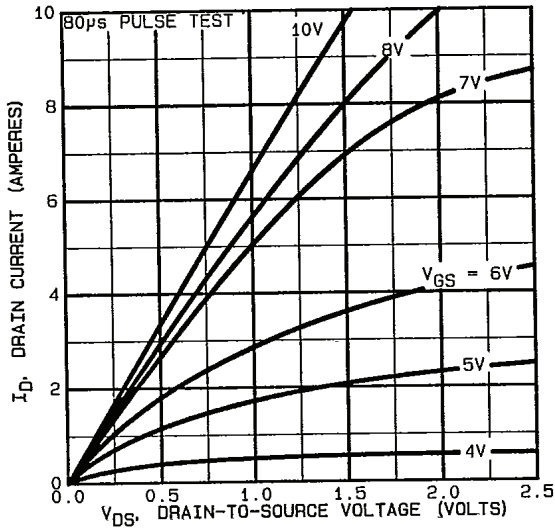


Fig. 2 - Typical Output Characteristics

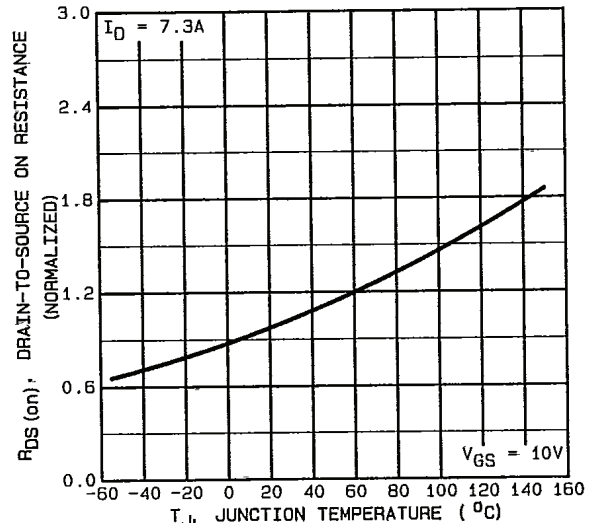


Fig. 4 - Normalized On-Resistance vs. Temperature

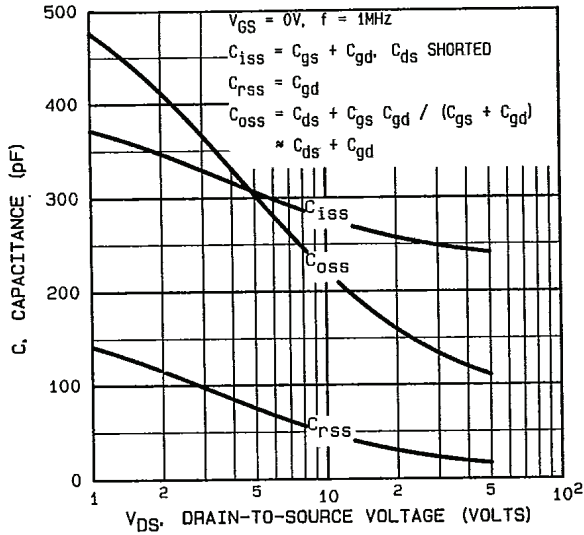


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

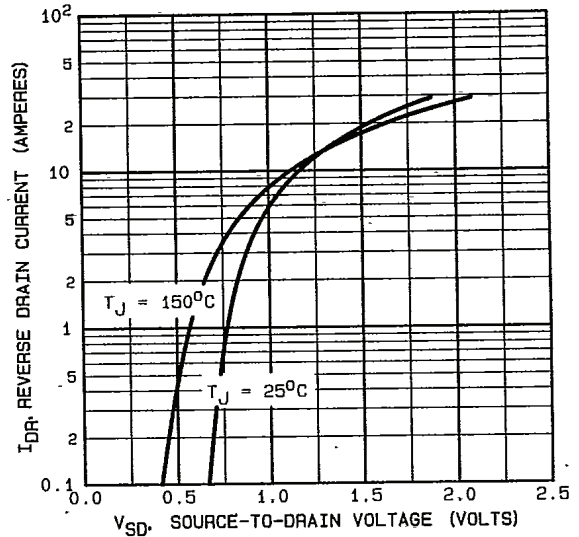


Fig. 7 - Typical Source-Drain Diode Forward Voltage

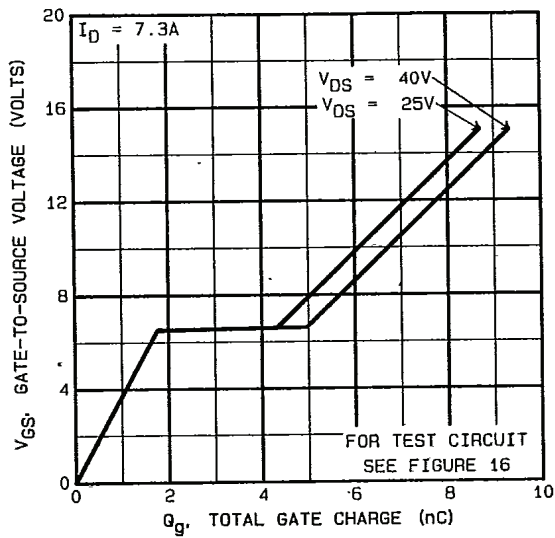


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

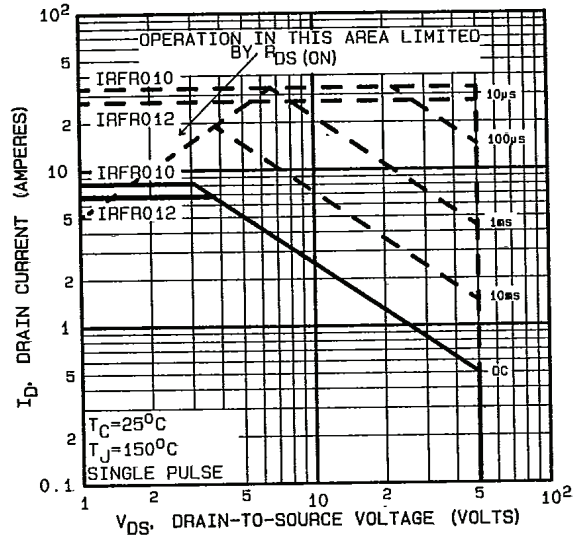


Fig. 8 - Maximum Safe Operating Area



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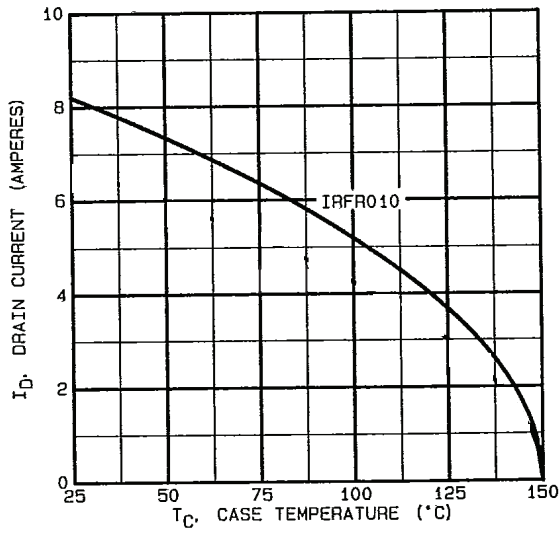


Fig. 9 - Maximum Drain Current vs. Case Temperature

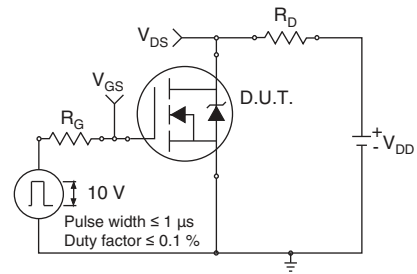


Fig. 10a - Switching Time Test Circuit

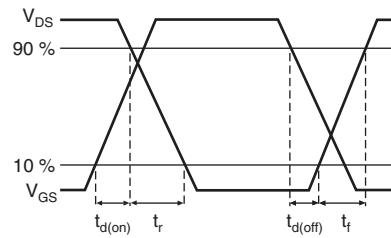


Fig. 10b - Switching Time Waveforms

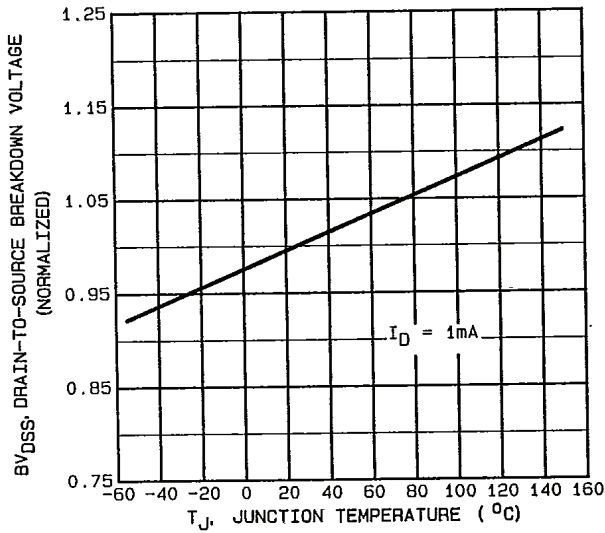


Fig. 10 - Breakdown Voltage vs. Temperature

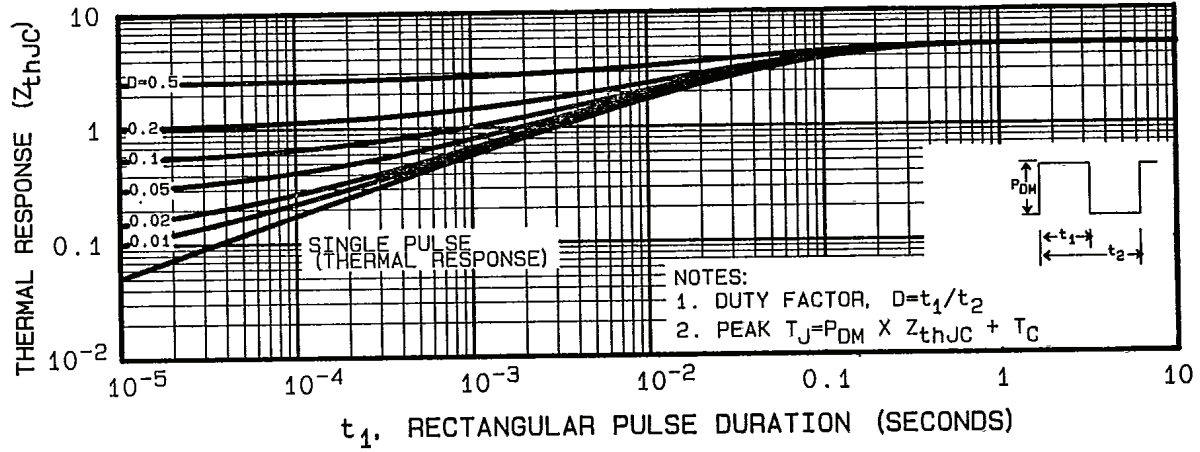


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

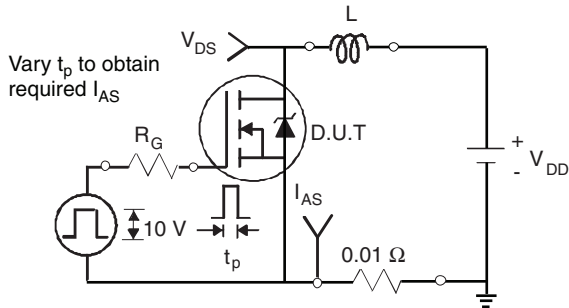


Fig. 12a - Unclamped Inductive Test Circuit

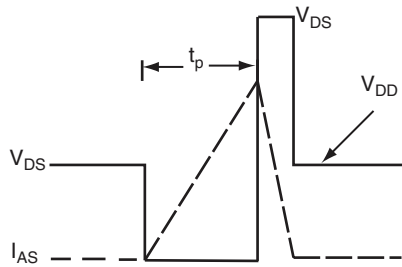


Fig. 12b - Unclamped Inductive Waveforms

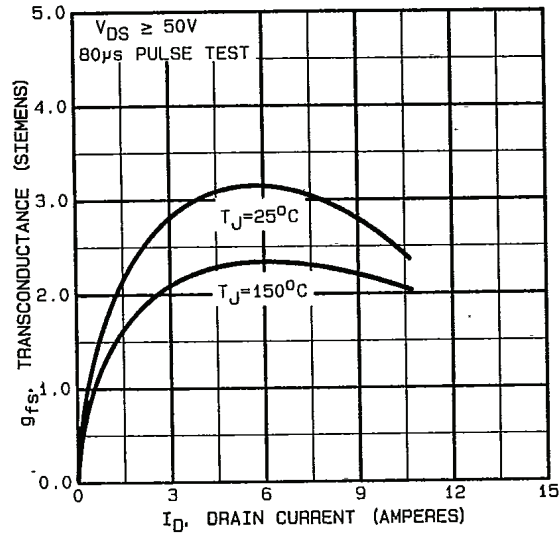


Fig. 12c - Typical Transconductance vs. Drain Current

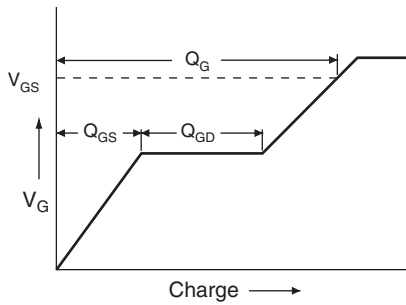


Fig. 13a - Basic Gate Charge Waveform

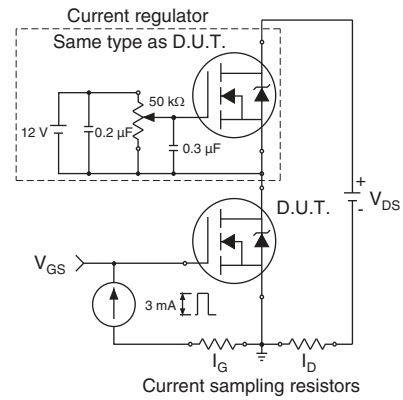
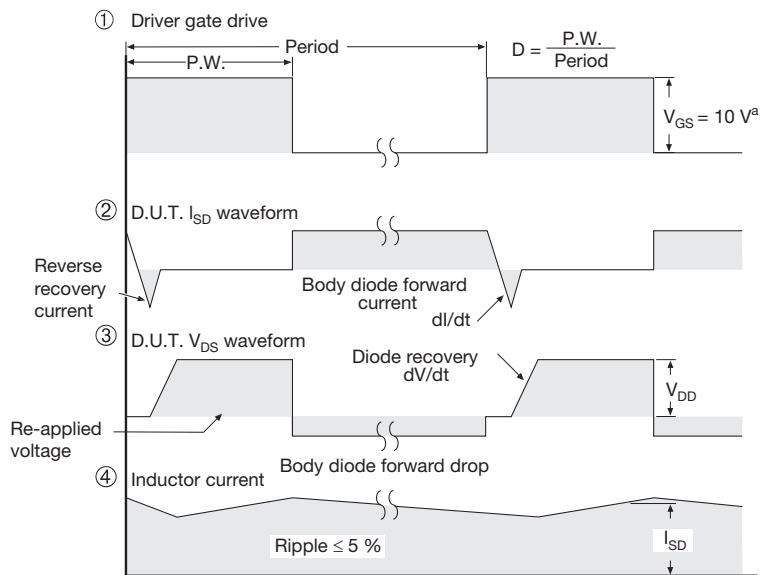
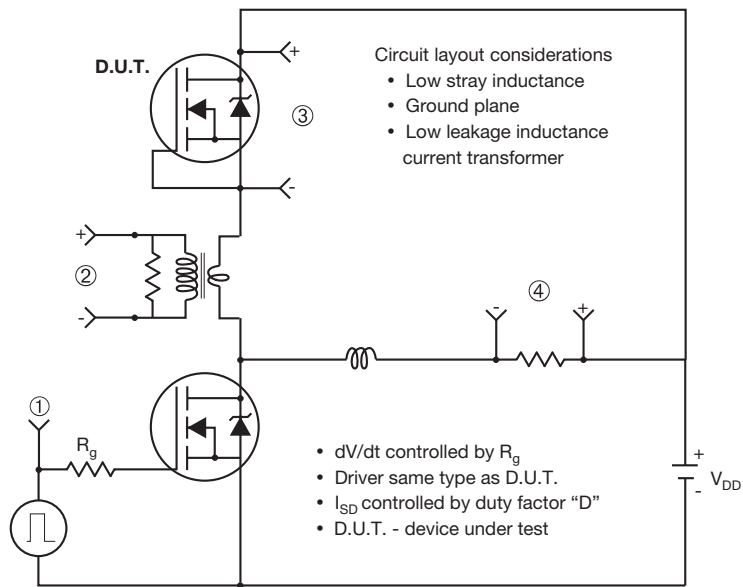


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel